

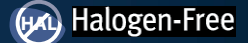
EPC2212 - Automotive 100 V (D-S) Enhancement Mode Power Transistor

 V_{DS} , 100 V

 $R_{DS(on)}$, 13.5 mΩ

 I_D , 18 A

AEC-Q101



Gallium Nitride's exceptionally high electron mobility and low temperature coefficient allows very low $R_{DS(on)}$, while its lateral device structure and majority carrier diode provide exceptionally low Q_G and zero Q_{RR} . The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.

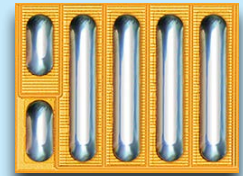
Maximum Ratings			
PARAMETER		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage (Continuous)	100	V
I_D	Continuous ($T_A = 25^\circ\text{C}$)	18	A
	Pulsed (25°C , $T_{PULSE} = 300 \mu\text{s}$)	75	
V_{GS}	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	
T_J	Operating Temperature	-40 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-40 to 150	

Thermal Characteristics			
PARAMETER		TYP	UNIT
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2	$^\circ\text{C}/\text{W}$
$R_{\theta JB}$	Thermal Resistance, Junction-to-Board	4	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	69	

Note 1: $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board. See https://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf for details.

Static Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise stated)						
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-to-Source Voltage	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	100			V
I_{DSS}	Drain-Source Leakage	$V_{DS} = 100 \text{ V}$, $V_{GS} = 0 \text{ V}$		10	250	μA
I_{GSS}	Gate-to-Source Forward Leakage	$V_{GS} = 6 \text{ V}$, $T_J = 25^\circ\text{C}$		0.005	1.8	mA
	Gate-to-Source Forward Leakage [#]	$V_{GS} = 6 \text{ V}$, $T_J = 125^\circ\text{C}$		0.015	3	
	Gate-to-Source Reverse Leakage	$V_{GS} = -4 \text{ V}$		10	250	μA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 3 \text{ mA}$	0.7	1	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	$V_{GS} = 5 \text{ V}$, $I_D = 11 \text{ A}$		10	13.5	mΩ
V_{SD}	Source-Drain Forward Voltage [#]	$I_S = 0.5 \text{ A}$, $V_{GS} = 0 \text{ V}$		1.5		V

All measurements were done with substrate connected to source.
[#] Defined by design. Not subject to production test.



Die size: 2.1 x 1.6 mm

EPC2212 eGaN® FETs are supplied only in passivated die form with solder bars.

Applications

- Lidar/Pulsed Power Applications
- High Power Density DC-DC Converters
- Class-D Audio
- High Intensity Headlamps

Benefits

- Ultra High Efficiency
- Ultra Low $R_{DS(on)}$
- Ultra Low Q_G
- Ultra Small Footprint

Scan QR code or click link below for more information including reliability reports, device models, demo boards!



<https://l.ead.me/EPC2212>

Dynamic Characteristics# ($T_J = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{ISS}	Input Capacitance	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$		339	407	pF
C_{RSS}	Reverse Transfer Capacitance			3		
C_{OSS}	Output Capacitance			238	357	
$C_{OSS(ER)}$	Effective Output Capacitance, Energy Related (Note 2)	$V_{DS} = 0\text{ to }50\text{ V}, V_{GS} = 0\text{ V}$		292		
$C_{OSS(TR)}$	Effective Output Capacitance, Time Related (Note 3)			359		
R_G	Gate Resistance			0.4		Ω
Q_G	Total Gate Charge	$V_{DS} = 50\text{ V}, V_{GS} = 5\text{ V}, I_D = 11\text{ A}$		3.2	4	nC
Q_{GS}	Gate-to-Source Charge	$V_{DS} = 50\text{ V}, I_D = 11\text{ A}$		0.9		
Q_{GD}	Gate-to-Drain Charge			0.6		
$Q_{G(TH)}$	Gate Charge at Threshold			0.55		
Q_{OSS}	Output Charge	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$		18	27	
Q_{RR}	Source-Drain Recovery Charge			0		

Defined by design. Not subject to production test.

All measurements were done with substrate connected to source.

Note 2: $C_{OSS(ER)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS} .

Note 3: $C_{OSS(TR)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS} .

Figure 1: Typical Output Characteristics at 25°C

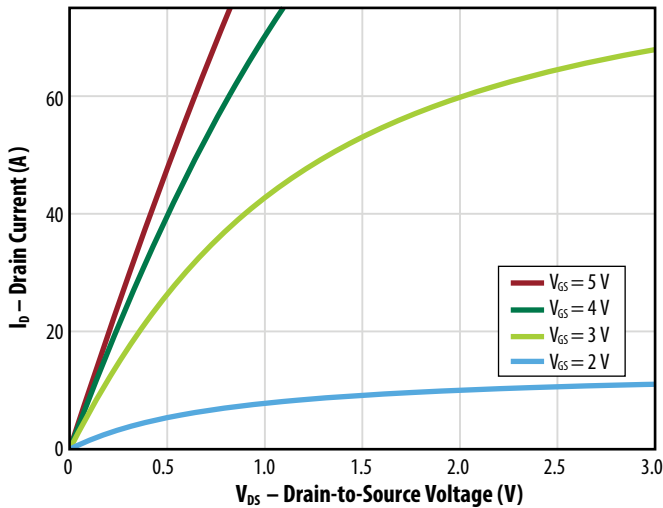


Figure 2: Typical Transfer Characteristics

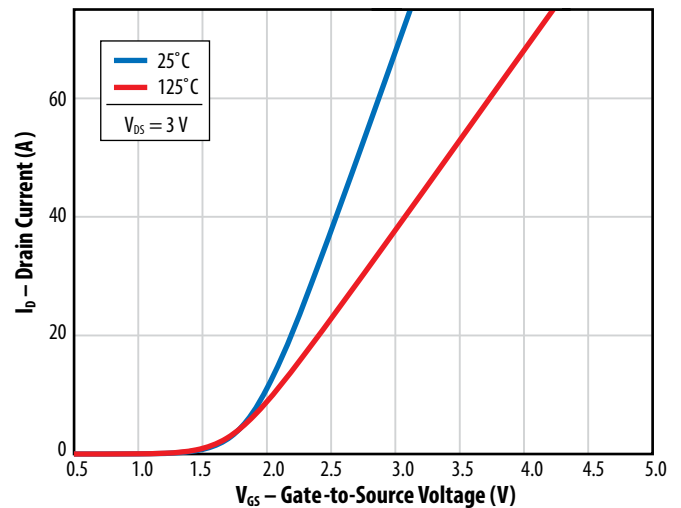


Figure 3: $R_{DS(on)}$ vs. V_{GS} for Various Drain Currents

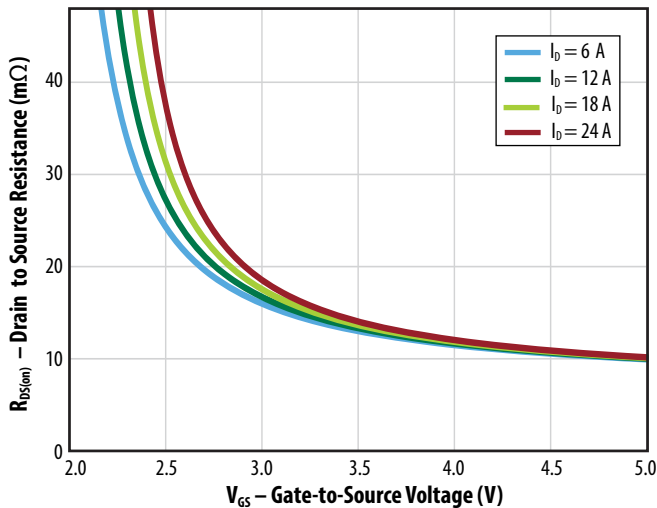


Figure 4: $R_{DS(on)}$ vs. V_{GS} for Various Temperatures

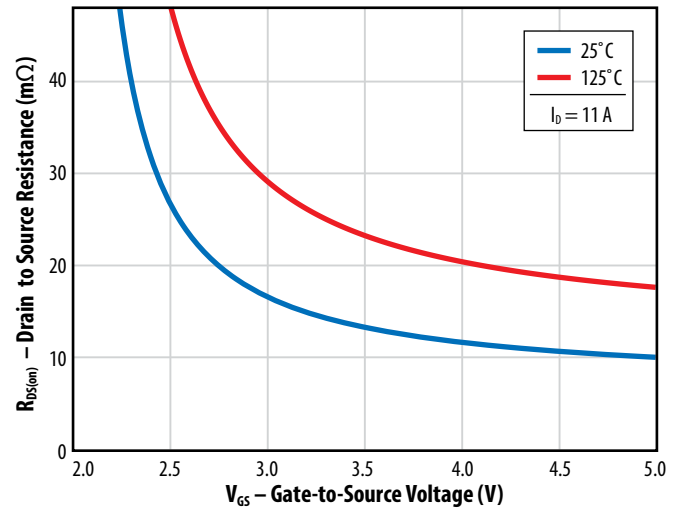


Figure 5a: Typical Capacitance (Linear Scale)

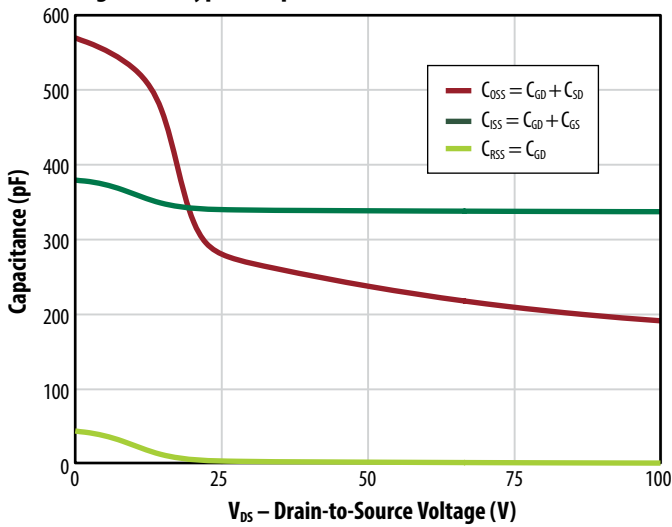


Figure 5b: Typical Capacitance (Log Scale)

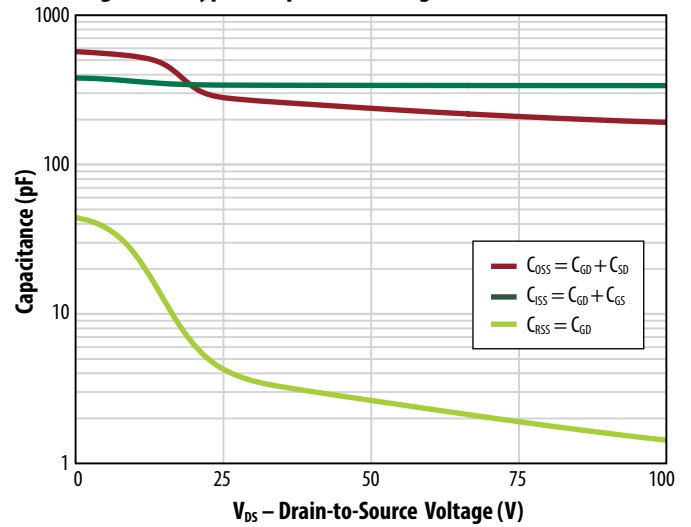


Figure 6: Typical Output Charge and C_{oss} Stored Energy

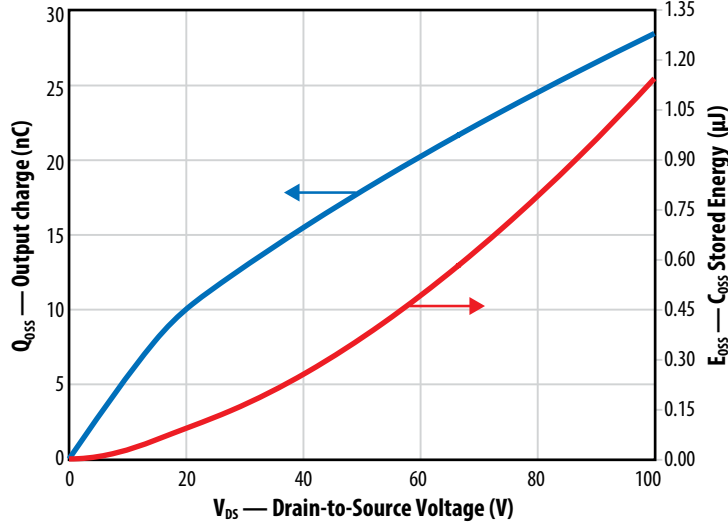


Figure 7: Typical Gate Charge

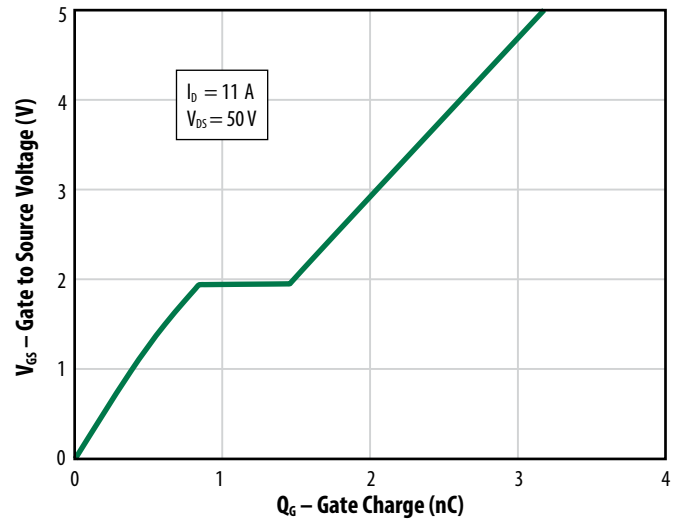


Figure 8: Reverse Drain-Source Characteristics

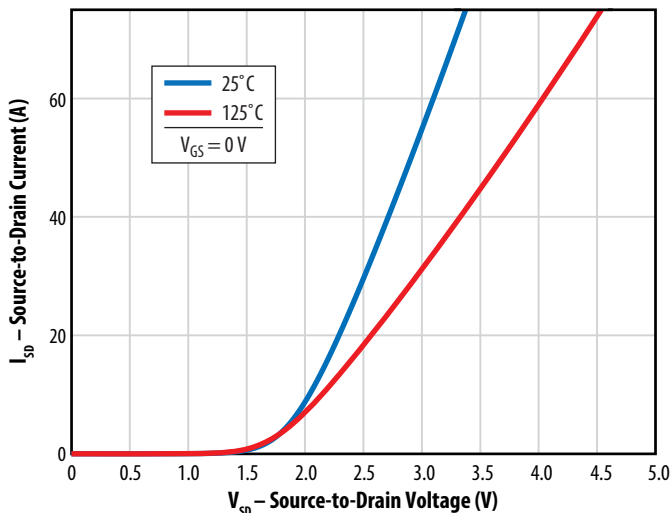
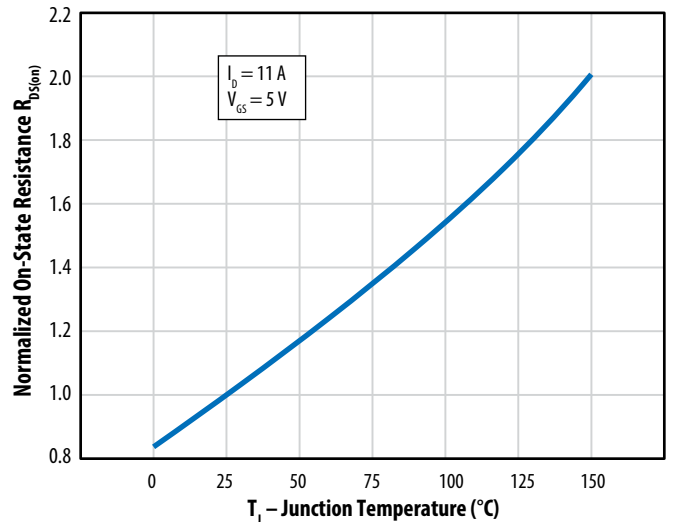


Figure 9: Normalized On-State Resistance vs. Temperature



Note: Negative gate drive voltage increases the reverse drain-source voltage. EPC recommends 0 V for OFF.

Figure 10: Normalized Threshold Voltage vs. Temperature

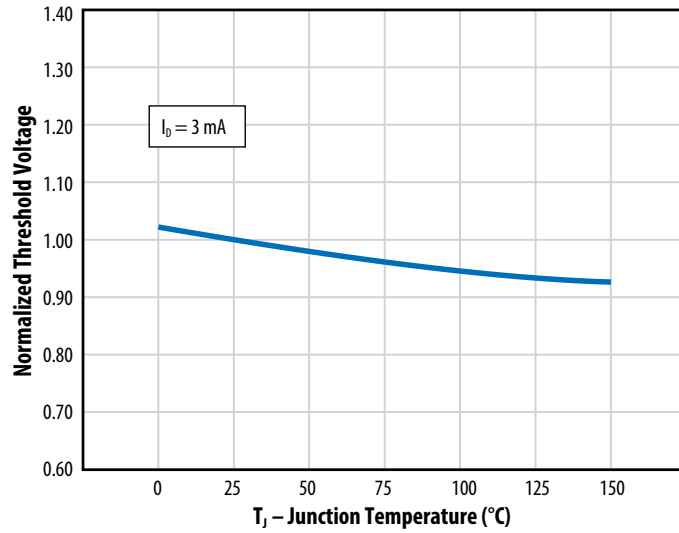


Figure 11: Transient Thermal Response Curves

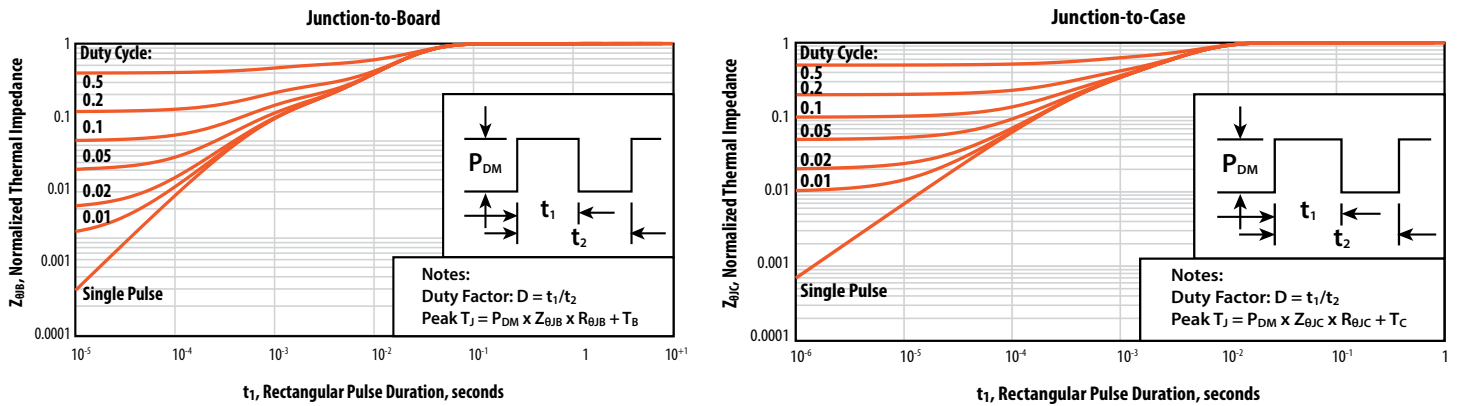
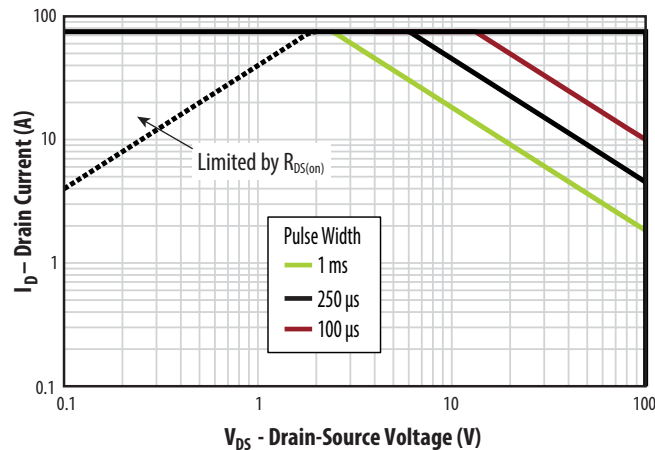
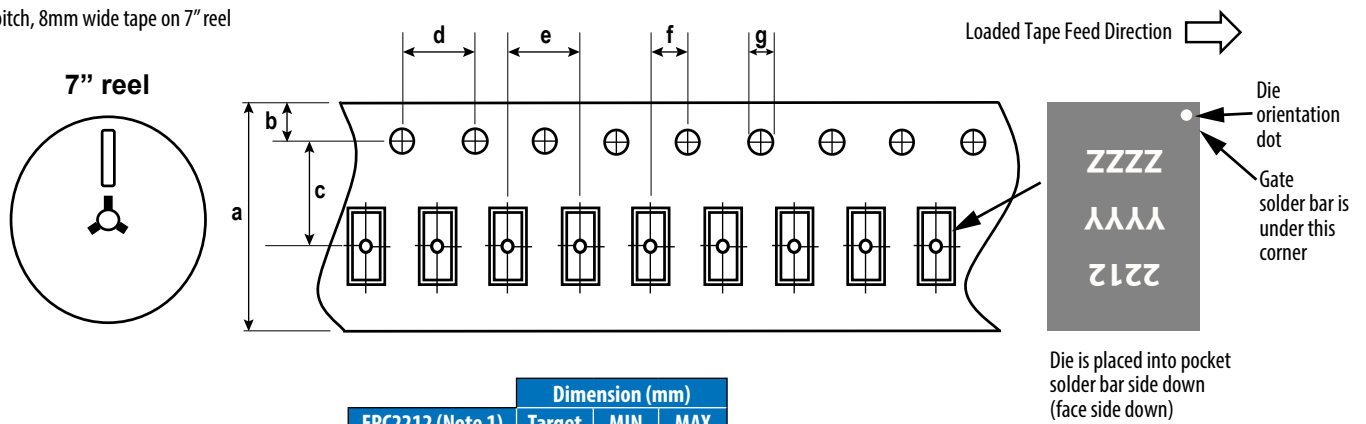


Figure 12: Safe Operating Area



TAPE AND REEL CONFIGURATION

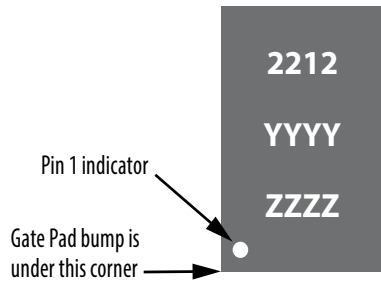
4mm pitch, 8mm wide tape on 7" reel



EPC2212 (Note 1)	Dimension (mm)		
	Target	MIN	MAX
a	8.00	7.90	8.30
b	1.75	1.65	1.85
c (Note 2)	3.50	3.45	3.55
d	4.00	3.90	4.10
e	4.00	3.90	4.10
f (Note 2)	2.00	1.95	2.05
g	1.50	1.50	1.60

Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/JEDEC industry standard.
 Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

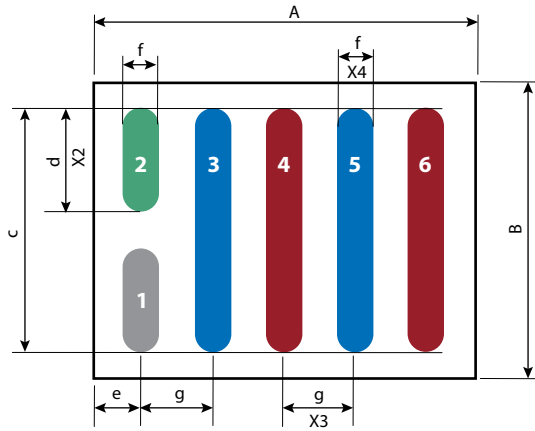
DIE MARKINGS



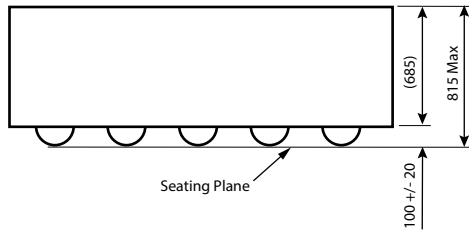
Part Number	Laser Markings		
	Part # Marking Line 1	Lot_Date Code Marking Line 2	Lot_Date Code Marking Line 3
EPC2212	2212	YYYY	ZZZZ

DIE OUTLINE

Solder Bar View



Side View



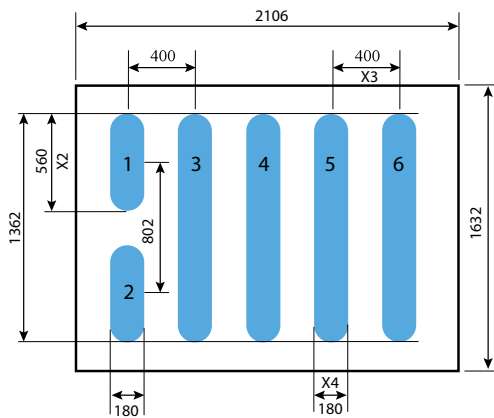
DIM	MICROMETERS		
	MIN	Nominal	MAX
A	2076	2106	2136
B	1602	1632	1662
c	1379	1382	1385
d	577	580	583
e	235	250	265
f	195	200	205
g	400	400	400

Pad no. 1 is Gate;
 Pads no. 3, 5 are Drain;
 Pads no. 4, 6 are Source;
 Pad no. 2 is Substrate.*

*Substrate pin should be connected to Source

RECOMMENDED LAND PATTERN

(units in μm)



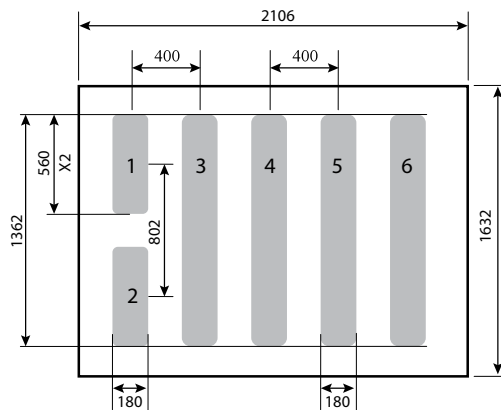
The land pattern is solder mask defined.

Pad no. 1 is Gate;
 Pads no. 3, 5 are Drain;
 Pads no. 4, 6 are Source;
 Pad no. 2 is Substrate.*

*Substrate pin should be connected to Source

RECOMMENDED STENCIL DRAWING

(measurements in μm)



Recommended stencil should be 4mil (100 μm) thick, must be laser cut, opening per drawing. The corner has a radius of R60

Intended for use with SAC305 Type 4 solder, reference 88.5% metals content.

Additional assembly resources available at <https://epc-co.com/epc/DesignSupport/AssemblyBasics.aspx>


Efficient Power Conversion Corporation (EPC) reserves the right to make changes without further notice to any products herein to improve reliability, function or design. EPC does not assume any liability arising out of the application or use of any product or circuit described herein; neither does it convey any license under its patent rights, nor the rights of others.

eGaN® is a registered trademark of Efficient Power Conversion Corporation.
 EPC Patent Listing: epc-co.com/epc/AboutEPC/Patents.aspx

Information subject to change without notice.
 Revised February, 2023

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

 [View EPC2212 on WIN SOURCE](#)

 [EPCOS \(TDK\) Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management